



Valley and Spin Blockade in Graphene Quantum Dots

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Motivation:

Towards Graphene Quantum Dot Qubits

Graphene quantum dots:

- low spin-orbit interaction
 - hyperfine interaction
 - 2-fold spin and 2-fold valley degrees of freedom
- long spin coherence time[1]

→ Promising for spin/valley quantum dot qubits

Spin \uparrow, \downarrow Valley K^-, K^+

• Spins in a magnetic field B :

$$\Delta E_{\uparrow}: +\frac{1}{2}g_s\mu_B B$$

$$\Delta E_{\downarrow}: -\frac{1}{2}g_s\mu_B B,$$

where $g_s = 2$.

• Valleys in a perpendicular magnetic field B (low field limit):

$$\Delta E_{K^+}: +\frac{1}{2}g_v\mu_B B$$

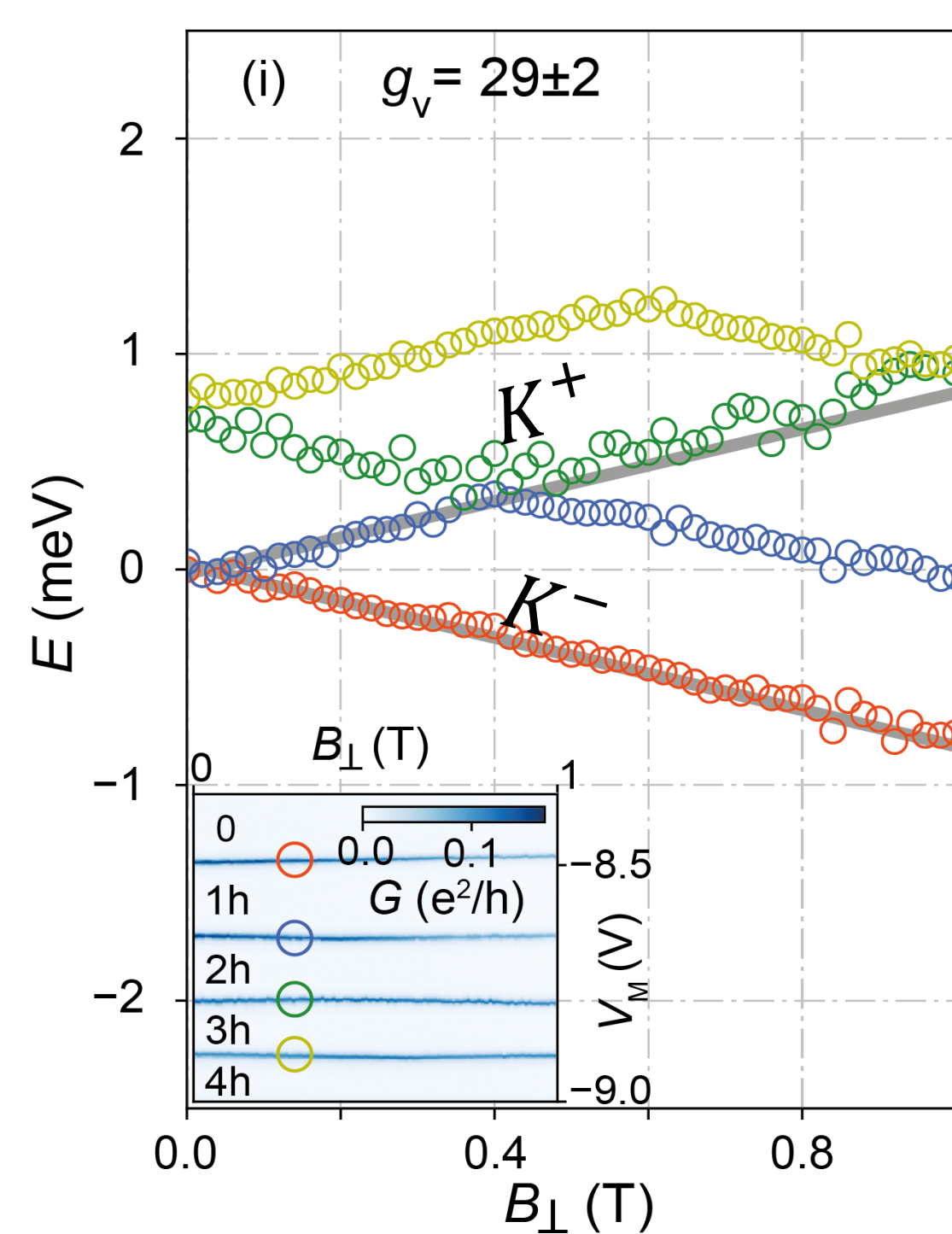
$$\Delta E_{K^-}: -\frac{1}{2}g_v\mu_B B,$$

where $g_v \sim 20 - 90$ is:

- dependent on dot size

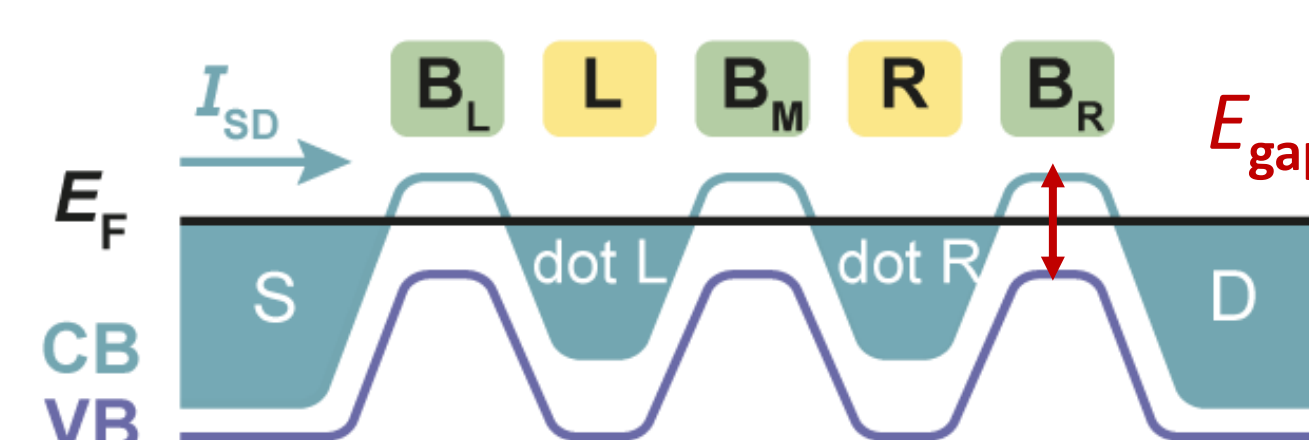
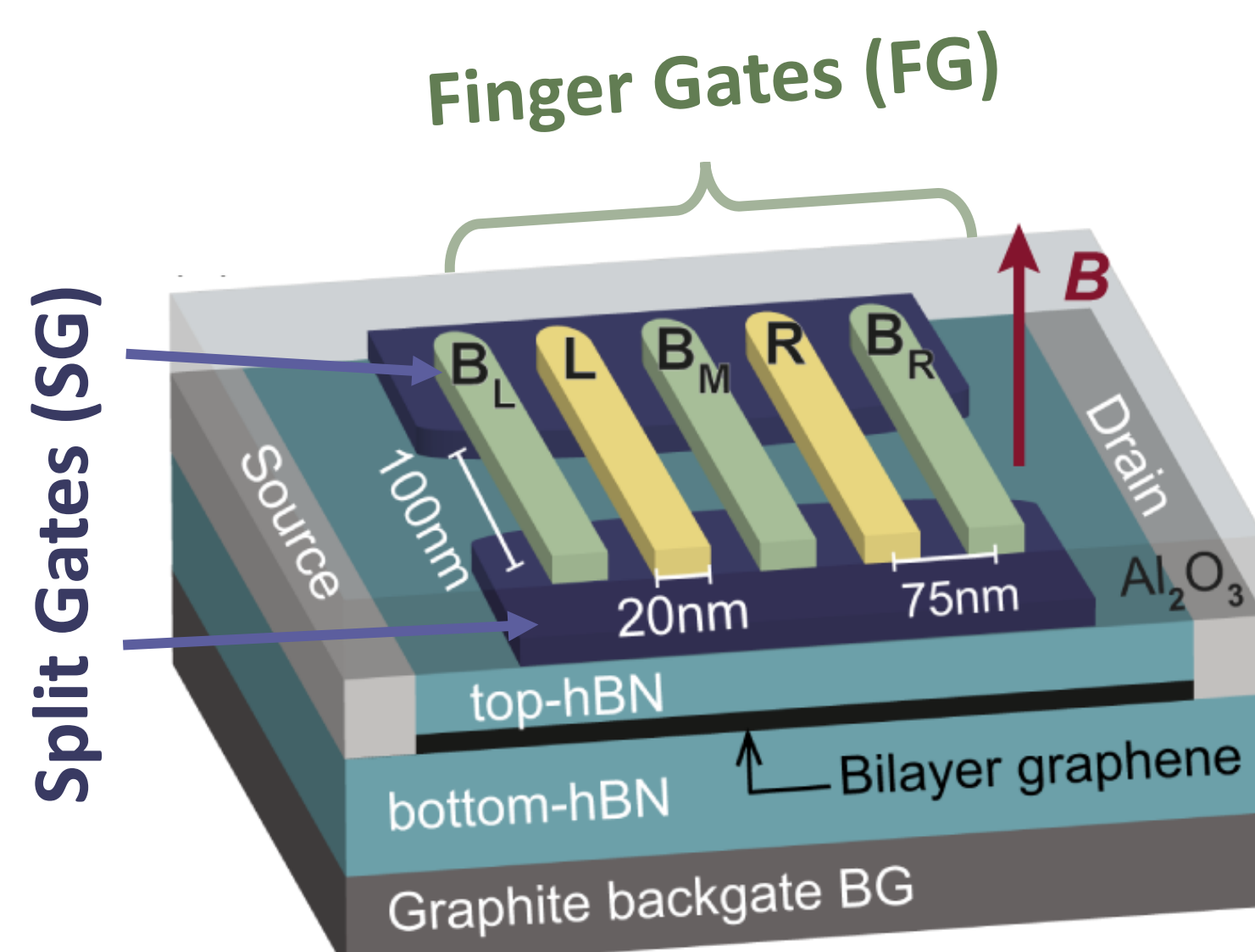
and BLG gap size

(both gate voltage tunable *in situ*)



Single particle level spectrum extracted from Coulomb resonances [3].

Formation of Bilayer Graphene Quantum Dots



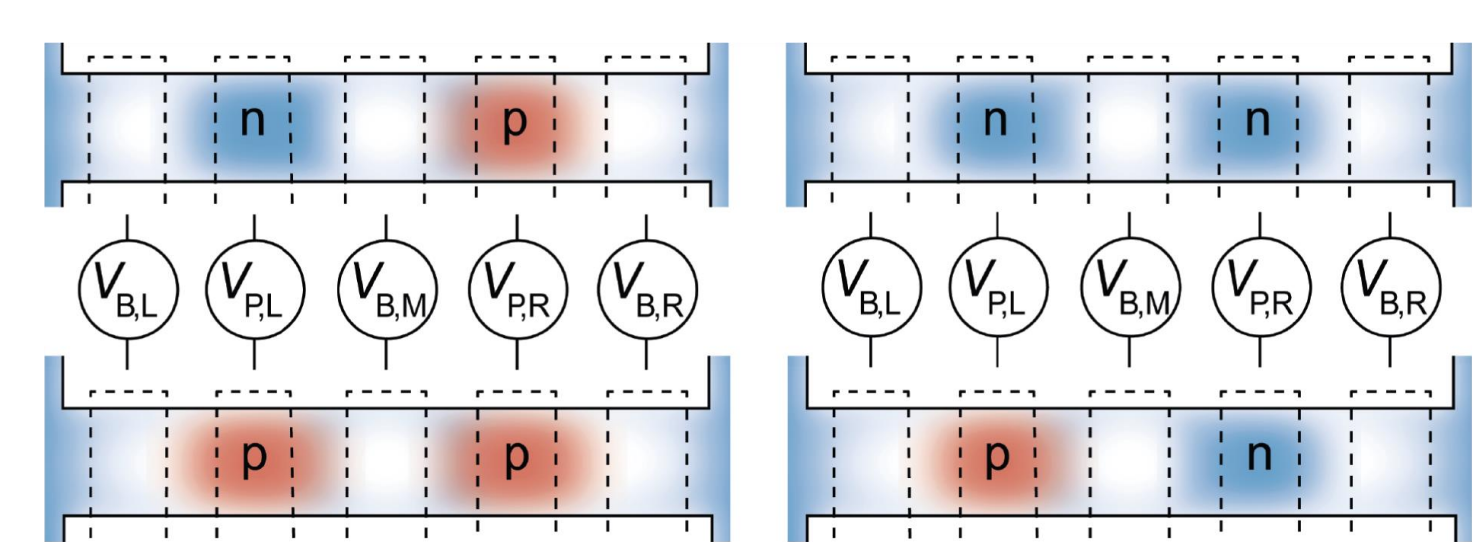
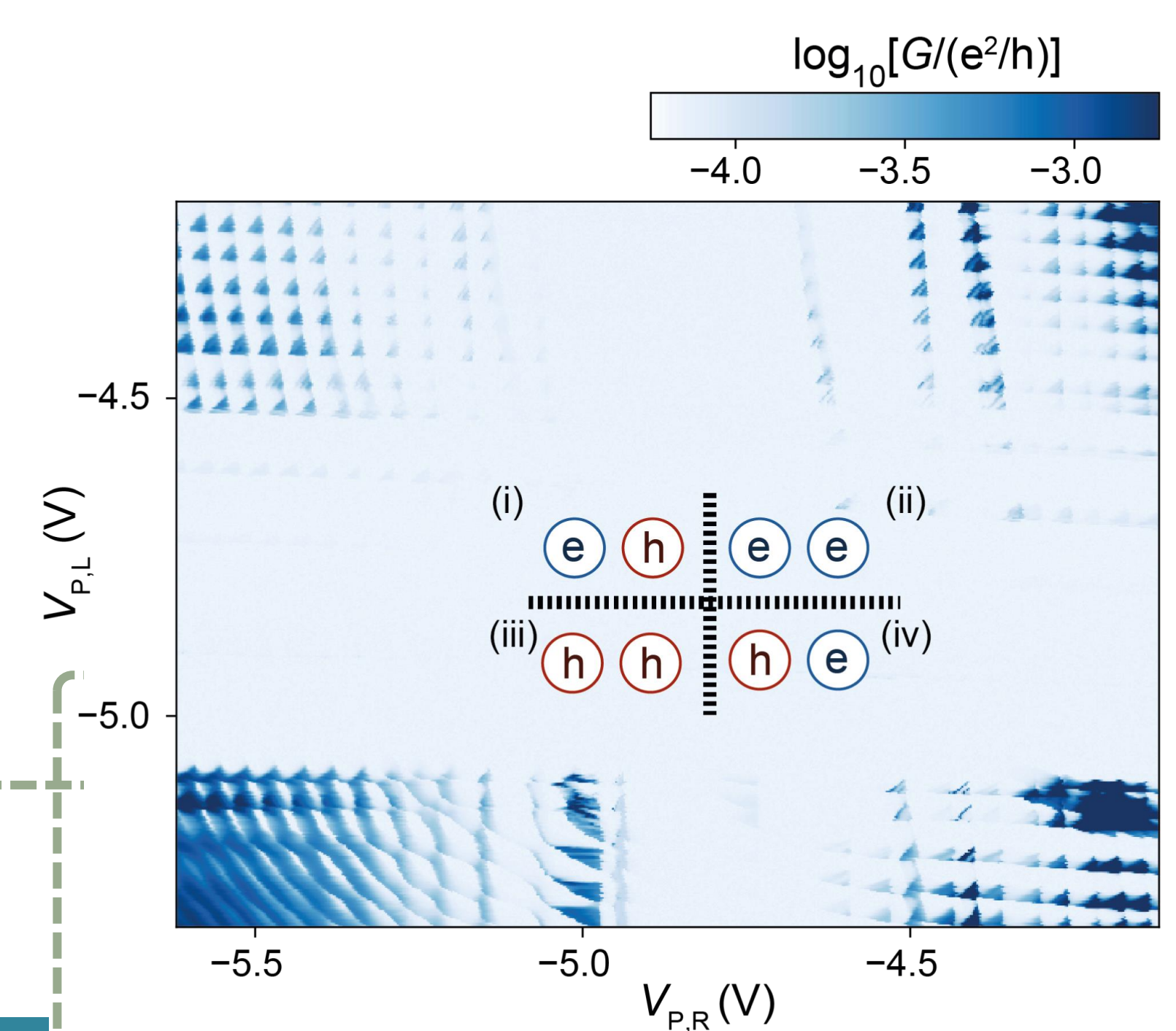
- Define gaps as tunnel barriers by barrier gate voltages V_{Bs}
- Switch between hole \leftrightarrow electron dot by plunger gate voltages $V_{L,R}$.

→ Double dots with reversible polarity

Bilayer Graphene (BLG):

- Electric field perpendicular to BLG opens a band gap E_{gap} [2]
- Device = Van der Waals stack + metallic gate
- Top- + back-gates opens bandgap E_{gap} + tune Fermi energy E_F :
→ Split gates define a conducting channel
→ Finger gates tune the channel locally

e.g. +ve V_{BG} & -ve V_{SG} & -ve V_{FGS}
→ *n*-type double dots in *n*-type channel



Double dot charge stability diagram [3], with $V_{bias} = 2$ mV.

Peculiar two-particle states & Pauli Spin and Valley Blockade

- From excited-state measurements for 2 particles in one dot [4] **(2,0)**:

(A): low-field ground state:

Spin-triplet valley-triplet: $|T_s^-\rangle|S_v\rangle$

+ One exchange energy E_{ch} above:

Spin-singlet valley-triplet: $|S_s\rangle|T_v^{-,+}\rangle$

Perpendicular B field couples to the valleys and lower $|S_s\rangle|T_v^-$ by $2\Delta E_{K^-}$:

(B): high-field ground state:

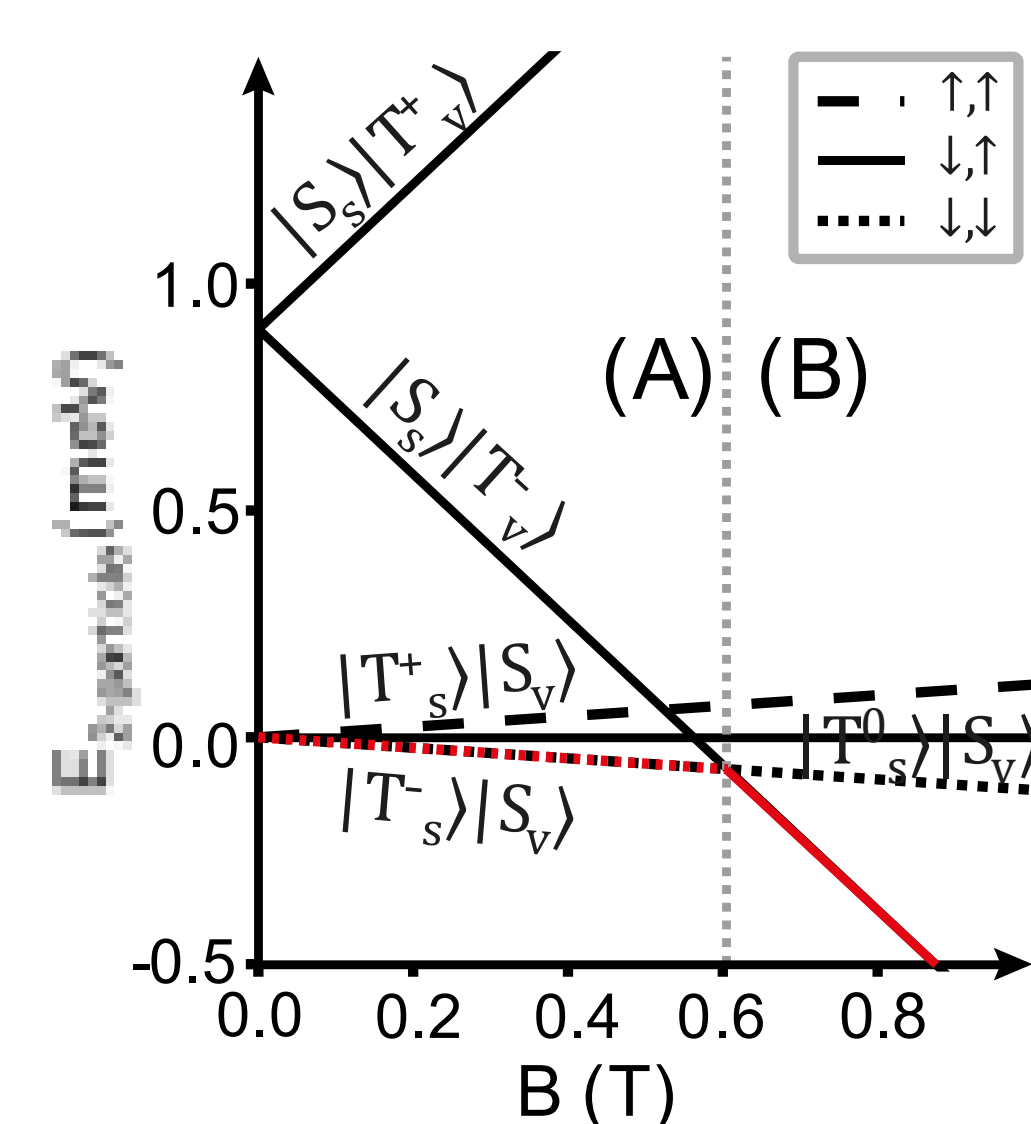
Spin-triplet valley-triplet: $|S_s\rangle|T_v^-$

+ $E_{ST} = 2\Delta E_{K^-} - E_{ch}$ above:

Spin-triplet valley-triplet: $|T_s^-\rangle|S_v\rangle$

- 2-particles each on one dot **(1,1)**, for weak enough interdot coupling:
→ two x 4 single-particle levels
→ 16 levels with 10 different energies

Ground state (always): $|\downarrow K^-\rangle|\downarrow K^-\rangle$



No (2,0) states match with quantum numbers of (1,1) ground state!

→ For $(1,1) \rightarrow (2,0)$ spin or valley flip always required

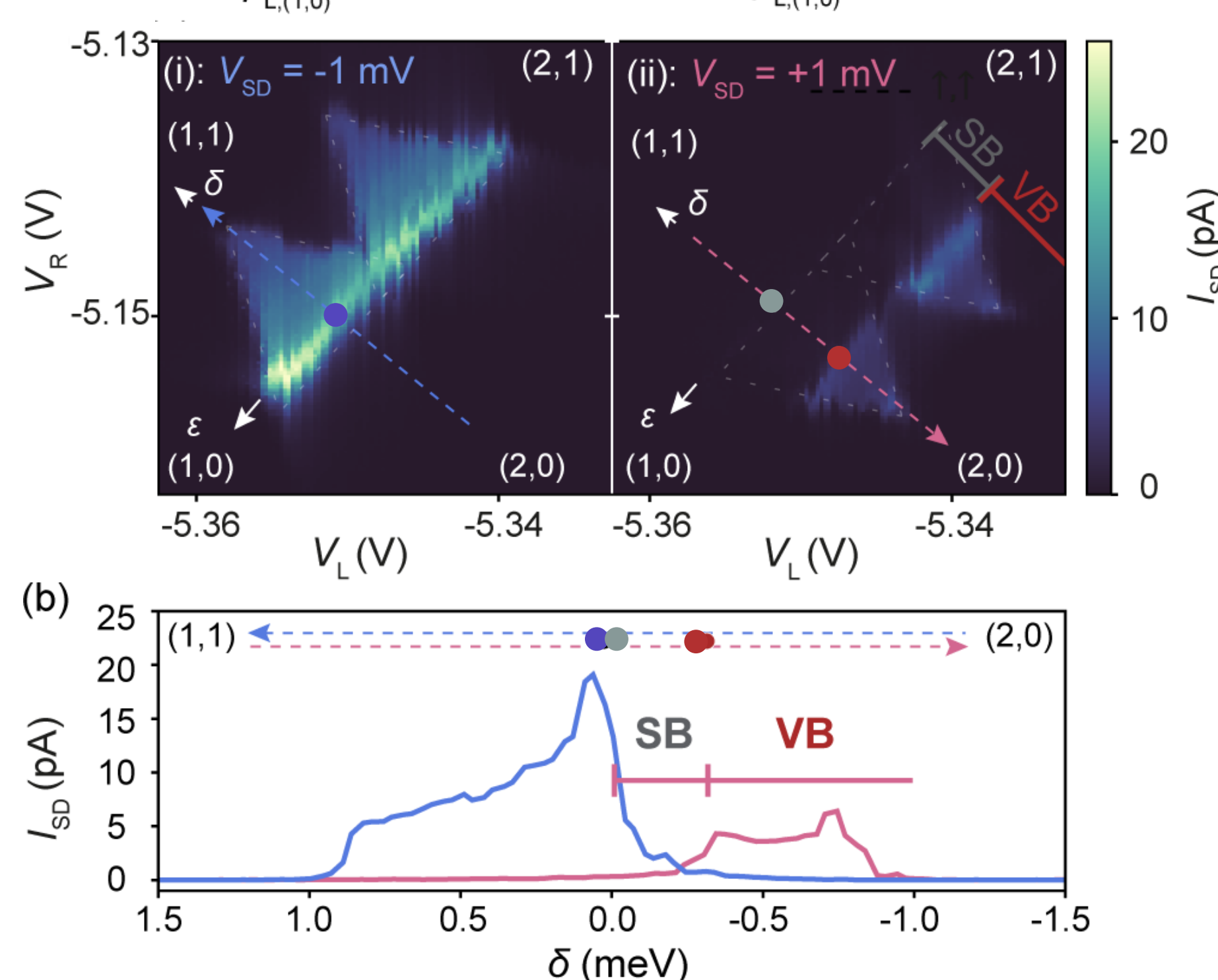
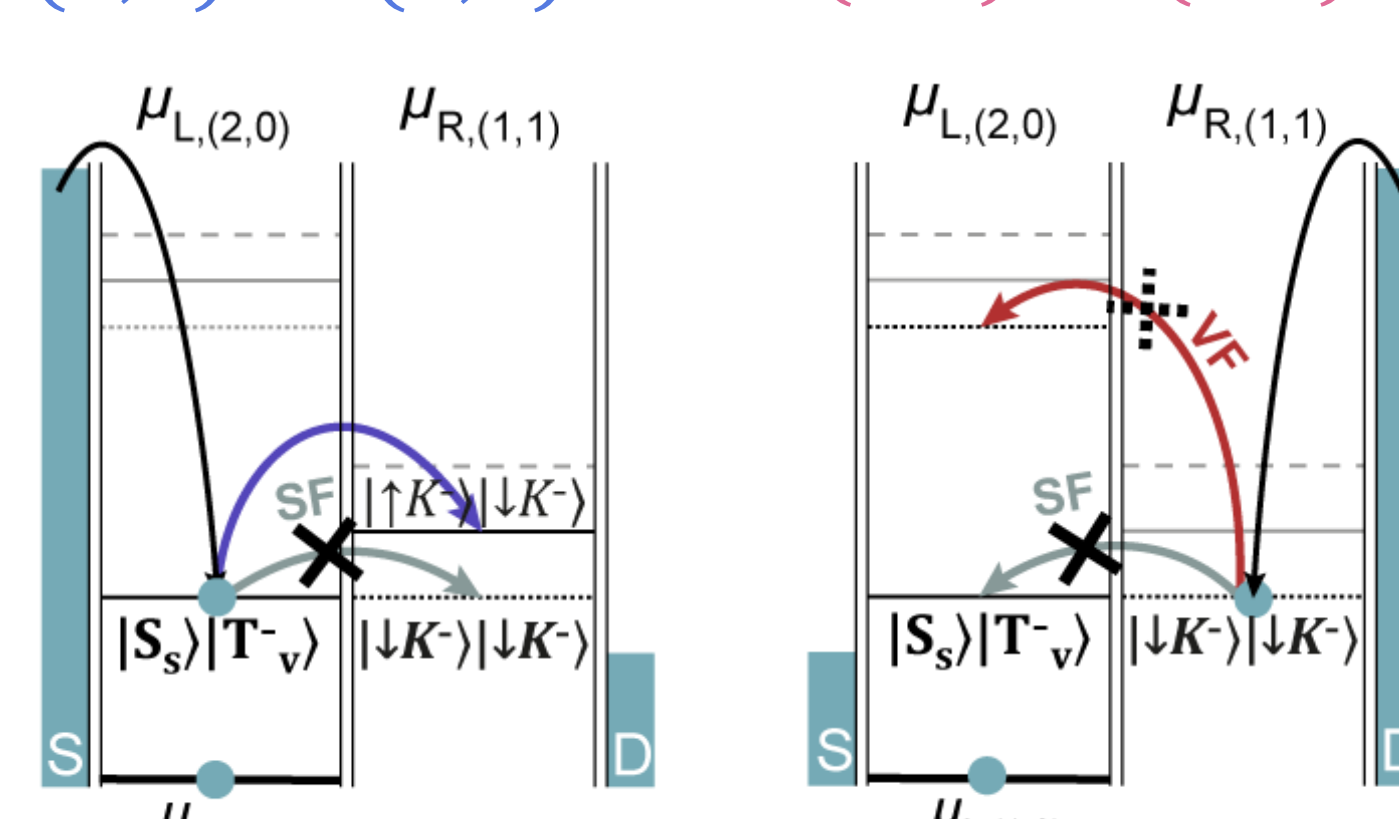
Change of GS for (2,0):
→ $(1,1) \rightarrow (2,0)$ valley blockade at low field, Spin blockade at high field

Spin blockade: suppresses current by > 50 times ($< 300fA$)

Valley blockade: suppresses current by 5 times

@ $B = 800mT$:

$(2,0) \rightarrow (1,1)$ $(1,1) \rightarrow (2,0)$



Conclusion & Outlook

- Mature graphene quantum dot technology
 - High quality samples
 - Gate tunable parameters (carrier occupancy, tunnel barrier, polarity, size, valley g-factor etc...)
 - Good understanding of QDs
- Robust Pauli spin and valley blockade
- Ready for spin and valley qubit manipulation and readouts

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